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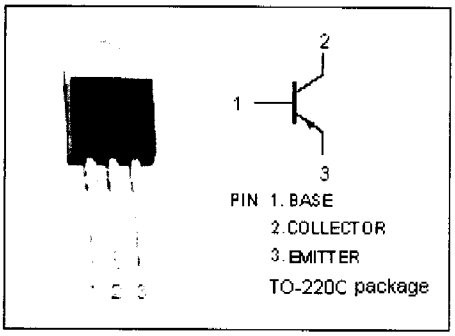
Silicon PNP Power Transistor

2SA1329



DESCRIPTION

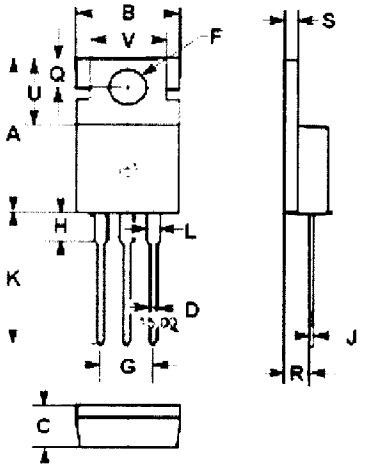
- Low Collector Saturation Voltage
  :$V_{CE(sat)}$= -0.4(V)(Max)@I_C= -6A
- High Switching Speed
- Complement to Type 2SC3346

APPLICATIONS

- Designed for high current switching applications.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-80	V
V_{CEO}	Collector-Emitter Voltage	-80	V
V_{EBO}	Emitter-Base Voltage	-6	V
I_C	Collector Current-Continuous	-12	A
I_B	Base Current-Continuous	-2	A
P_C	Total Power Dissipation @ T_C=25℃	40	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃



DIM	mm MIN	mm MAX
A	15.50	15.90
B	9.90	10.20
C	4.20	4.50
D	0.70	0.90
F	3.40	3.70
G	4.98	5.18
H	2.68	2.90
J	0.44	0.60
K	13.00	13.40
L	1.20	1.45
Q	2.70	2.90
R	2.30	2.70
S	1.29	1.35
U	6.45	6.65
V	8.66	8.86

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= -50mA ; I_B= 0	-80			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= -6A; I_B= -0.3A			-0.4	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= -6A; I_B= -0.3A			-1.2	V
I_{CBO}	Collector Cutoff Current	V_{CB}= -80V ; I_E= 0			-10	μ A
I_{EBO}	Emitter Cutoff Current	V_{EB}= -6V; I_C= 0			-10	μ A
h_{FE-1}	DC Current Gain	I_C= -1A ; V_{CE}= -1V	70		240	
h_{FE-2}	DC Current Gain	I_C= -6A ; V_{CE}= -1V	40			
f_T	Current-Gain—Bandwidth Product	I_C= -1A ; V_{CE}= -5V		50		MHz
C_{OB}	Output Capacitance	I_E= 0; V_{CB}= -10V; f_{test}= 1MHz		400		pF

Switching Times

t_{on}	Turn-on Time	R_L= 5Ω , I_{B1}= -I_{B2}= -0.3A, V_{CC}≒ -30V; Duty Cycle≤1%		0.3		μ s
t_{stg}	Storage Time			1.0		μ s
t_f	Fall Time			0.5		μ s

◆ h_{FE-1} Classifications

O	Y
70-140	120-240